Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor light emitting ~~element~~ diode comprising:

a first layer;

a semiconductor light emitting layer selectively provided on the first layer;

a current blocking layer of high resistance ~~provided around~~ surrounding the semiconductor light emitting layer on the first layer;

a second layer provided on the semiconductor light emitting layer and the current blocking layer;

a first electrode provided on the second layer; and

a second electrode provided on the back of the first layer,

a part of a light emitted from the semiconductor light emitting layer being emitted outside through the first layer, and

a part of the light emitted from the semiconductor light emitting layer being emitted outside through the second layer.

2. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 1, wherein a main component of the current blocking layer is same as a main component of the semiconductor light emitting layer, and the current blocking layer includes an impurity which is not included in the semiconductor light emitting layer.

3. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 1, wherein the current blocking layer is made of a semiconductor whose bandgap is wider than a bandgap of the semiconductor light emitting layer.

4. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 3, further comprising:

a first cladding layer which is provided between the first layer and the semiconductor light emitting layer and made of a semiconductor whose bandgap is wider than the bandgap of the semiconductor light emitting layer; and

a second cladding layer which is provided between the first layer and the semiconductor light emitting layer and made of a semiconductor whose bandgap is wider than the bandgap of the semiconductor light emitting layer,

wherein a refractive index of the current blocking layer is smaller than a refractive index of the light emitting layer, and the refractive index of the current blocking layer is greater than refractive indexes of the first and second cladding layers.

5. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 1, wherein at least one of the first and second layers has a slope on a side.

6. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 1, wherein:

at least one of the first and second layers is made of GaP, and

the semiconductor light emitting layer includes InGaAlP.

7. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 1, wherein at least one of the first and second layers is made of a material other than semiconductors.

8. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 1, wherein a lateral size of the semiconductor light emitting layer is 20 micrometers or less.

9. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 1, further comprising a conductive layer provided at least one of

between the first layer and the second electrode and between the second layer and the first electrode,

wherein the conduction layer is made of a material other than semiconductors and allows the light emitted from the semiconductor light emitting layer to pass therethrough.

10. (Currently Amended) A semiconductor light emitting ~~element~~ diode comprising:

a first layer;

a plurality of semiconductor light emitting layers selectively provided on the first layer, the semiconductor light emitting layers being separated from each other;

a current blocking layer of high resistance provided among the semiconductor light emitting layers on the first layer;

a second layer provided on the semiconductor light emitting layer and the current blocking layer;

a first electrode provided on the second layer; and

a second electrode provided on the back of the first layer,

a part of a light emitted from the semiconductor light emitting layers being emitted outside through the first layer, and

a part of the light emitted from the semiconductor light emitting layers being emitted outside through the second layer.

11. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 10, wherein a distance between the semiconductor light emitting layers is ~~great~~ greater near a center of the semiconductor light emitting ~~element, and~~

~~the distance between the semiconductor light emitting layers is small near edges~~ diode than a distance between the semiconductor light emitting layers near edges of the semiconductor light emitting ~~element~~ diode.

12. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 10, wherein a distance between the semiconductor light emitting

layers is ~~small~~ smaller near a center of the semiconductor light emitting ~~element, and~~

~~the distance between the semiconductor light emitting layers is great near edges~~ diode than a distance between the semiconductor light emitting layers near edges of the semiconductor light emitting ~~element~~ diode.

13. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 10, wherein a main component of the current blocking layer is same as a main component of the semiconductor light emitting layers, and the current blocking layer includes an impurity which is not included in the semiconductor light emitting layers.

14. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 10, wherein the current blocking layer is made of a semiconductor whose bandgap is wider than a bandgap of the semiconductor light emitting layers.

15. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 14, further comprising:

a first cladding layer which is provided between the first layer and the semiconductor light emitting layers and made of a semiconductor whose bandgap is wider than the bandgap of the semiconductor light emitting layers; and

a second cladding layer which is provided between the first layer and the semiconductor light emitting layers and made of a semiconductor whose bandgap is wider than the bandgap of the semiconductor light emitting layers,

wherein a refractive index of the current blocking layer is smaller than a refractive index of the light emitting layers, and the refractive index of the current blocking layer is greater than refractive indexes of the first and second cladding layers.

16. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 10, wherein at least one of the first and second layers has a slope on a side.

17. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 10, wherein:

at least one of the first and second layers is made of GaP, and

the semiconductor light emitting layers include InGaAlP.

18. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 10, wherein at least one of the first and second layers is made of a material other than semiconductors.

19. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 10, wherein a size of the semiconductor light emitting layers is 20 micrometers or less.

20. (Currently Amended) The semiconductor light emitting ~~element~~ diode according to claim 1, further comprising a conductive layer provided at least one of between the first layer and the second electrode and between the second layer and the first electrode,

wherein the conduction layer is made of a material other than semiconductors and allows the light emitted from the semiconductor light emitting layer to pass therethrough.

21. (New) The semiconductor light emitting diode according to clam 1, wherein a part of a light emitted from a side surface of the semiconductor light emitting layer is emitted outside through the current blocking layer.

22. (New) The semiconductor light emitting diode according to claim 10, wherein a part of a light emitted from side surfaces of the semiconductor light emitting layers is emitted outside through the current blocking layer.